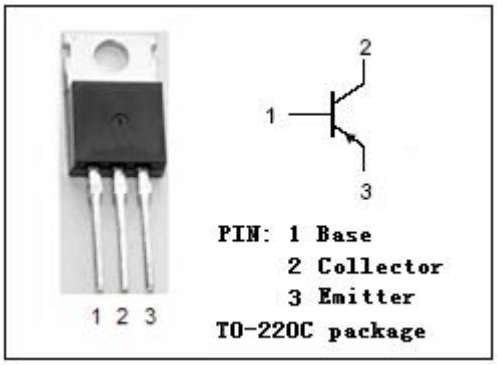
isc Silicon PNP Power Transistor — 2SB899



DESCRIPTION

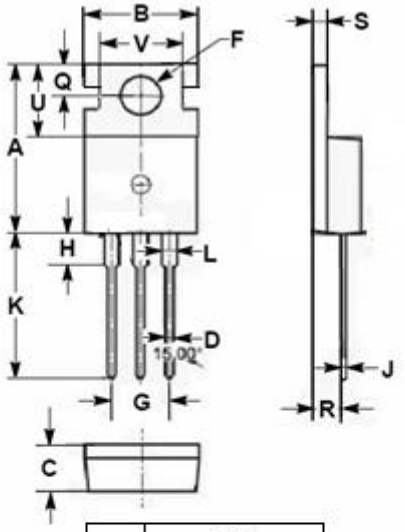
- Collector-Emitter BreakdownVoltage-
  : $V_{(BR)CEO}$= -50V(Min.)
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= -1.2(Max.) @I_C= -3A
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in general purpose amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-3	A
I_{CM}	Collector Current-Peak	-5	A
P_C	Collector Power Dissipation@T_C=25℃	25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA; R_{BE}= ∞	-50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA; I_C= 0	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -0.375A			-1.2	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -3A; V_{CE}= -4V			-1.8	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -50V; I_E= 0			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C= 0			-10	μA
h_{FE-1}	DC Current Gain	I_C= -1A; V_{CE}= -4V	50		200	
h_{FE-2}	DC Current Gain	I_C= -3A; V_{CE}= -4V	10			
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A ; V_{CE}= -10V	5			MHz